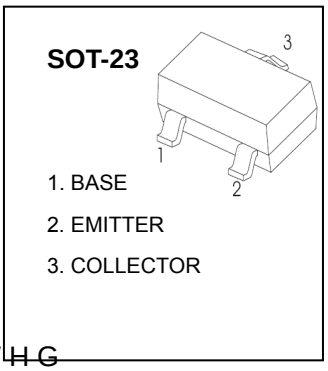
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

JC (T

SOT-23 Plastic-Encapsulate Transistors

2SC2412 TRANSISTOR (NPN)



FEATURES

· **Low C_{ob} ,C_{ob} = 2.0 pF (Typ).**

MARKING : BQ, BR, BS

0$;,0805$7,1*6 7 / XQOHVV RWKHUZLVH QRWHG

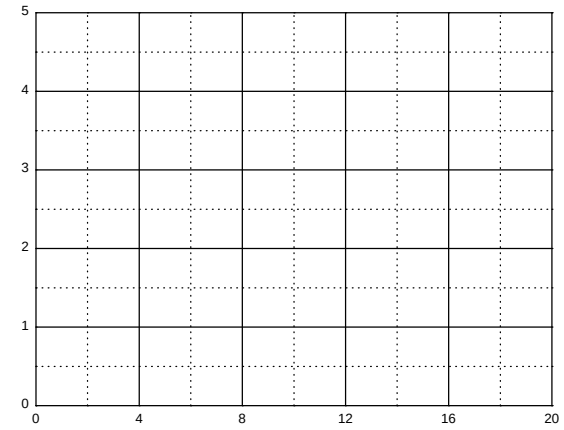
6\PERO	3DUDPHWHU	9DOXH	8QLW
9& % 2	&RO OHFWRU%DVH9RO WDJH		9
9& (2	&RO OHFWRU(PLWWHU 9RO WDJH		9
9(% 2	(PLWWHU%DVH9RO WDJH		9
,&	&RO OHFWRU &XUUHQW		P$
3&	&RO OHFWRU 3RZHU 'LVVLSDWLRQ		P:
5, - $	7KHUPDO 5HVLVWDQFH)URP-XQFWLRQ7R$PE		/ :
7M	-XQFWLRQ 7HPSHUDWXUH		/
7VWJ	6WRUDJH 7HPSHUDWXUH		/

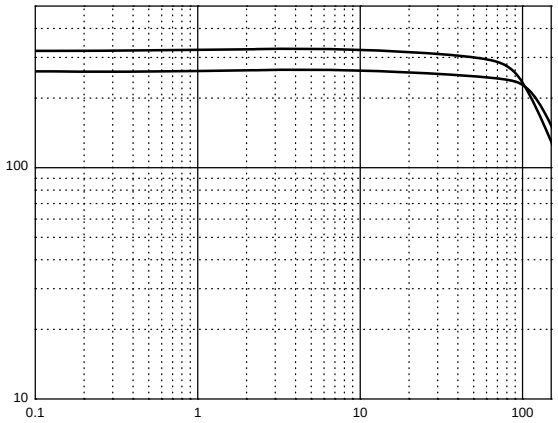
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

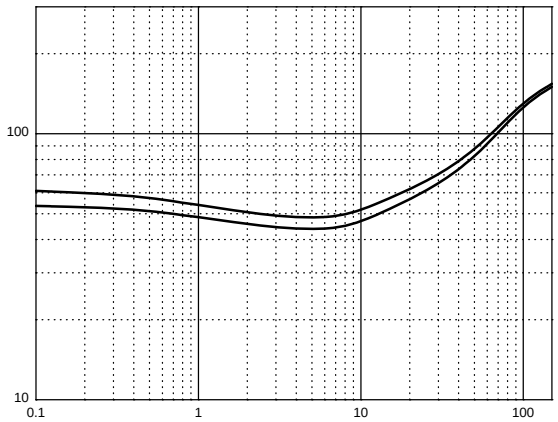
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=50μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50μA,I_C=0	7			V
Collector cut-off current	I_{CBO}	V_{CB}=60V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=7V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=6V,I_C=1mA	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA,I_B=5mA			0.4	V
Transition frequency	f_T	V_{CE}=12V,I_C=-2mA,f=100MHz		160		MHz
Collector output capacitance	C_{ob}	V_{CB}=12V,I_E=0,f=1MHz		2.0	3.5	pF

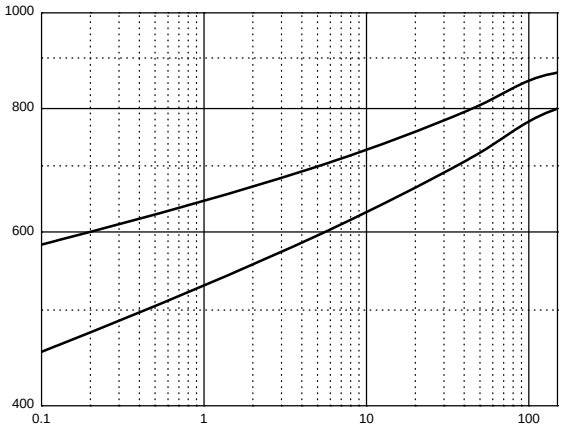
CLASSIFICATION OF h_{FE}

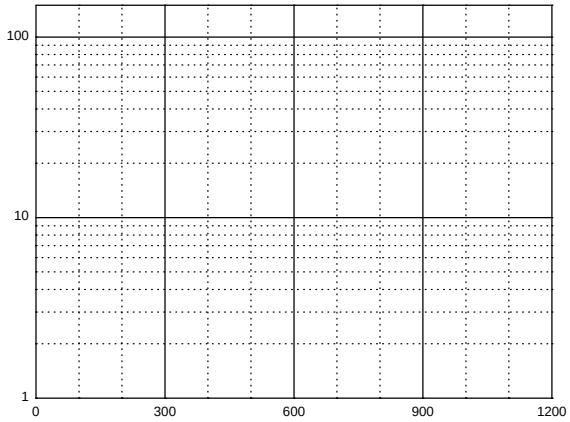
Rank	Q	R	S
Range	120 - 270	180 - 390	270 - 560
Marking	BQ	BR	BS

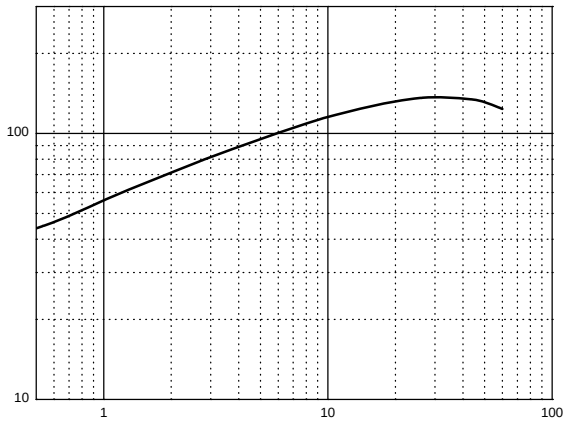

5
4
3
2
1
0
0
4
8
12
16
20

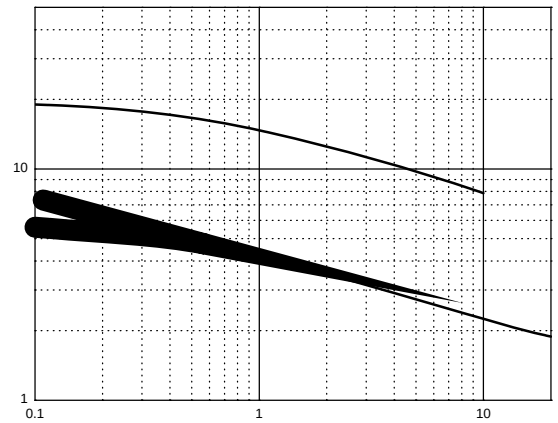

100
10
0.1
1
10
100

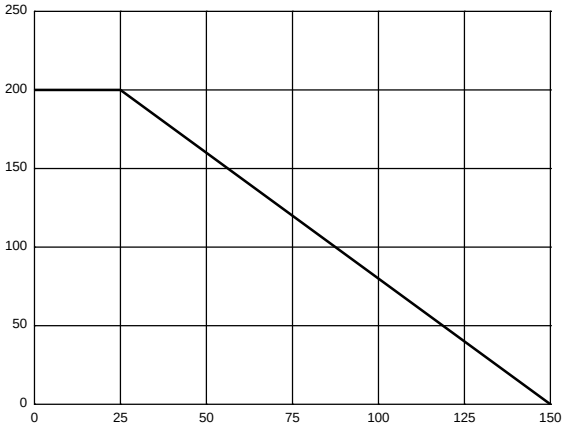

100
10
0.1
1
10
100


1000
800
600
400
0.1
1
10
100


100
10
1
0
300
600
900
1200


100
10
1
10
100


10
1
0.1
1
10


250
200
150
100
50
0
0
25
50
75
100
125
150

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

NOTICE

JCET re ments, improvements, corrections or other c


2000
1
1000
900